

1-Line Bi-directional TVS Diode

Features

- Operating voltage: 5V
- Low clamping voltage
- Low leakage current
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
Air discharge: $\pm 30\text{kV}$
Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 8A (8/20 μs)
- RoHS Compliant
- AEC-Q101 qualified

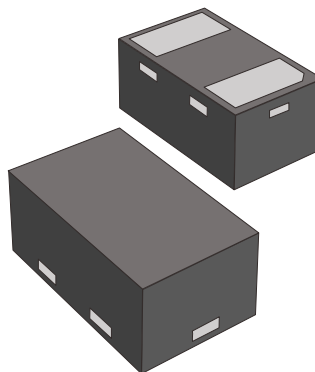
Applications

- Cell Phone Handsets and Accessories
- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Networking and Telecom
- Serial and Parallel Ports
- Peripherals

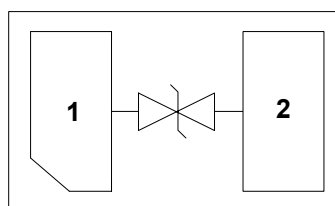
Mechanical Characteristics

- Package: DFN1006
- Lead Finish: Lead Free
- UL Flammability Classification Rating 94V-0
- Quantity Per Reel: 10,000 pcs
- Reel Size: 7 inch
- Device Marking: B2

Dimensions DFN1006



Pin Configuration



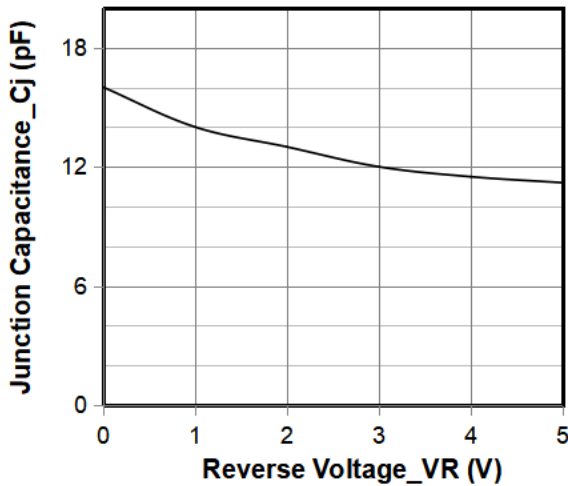
Absolute Maximum Ratings (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	P _{pp}	80	W
ESD per IEC 61000-4-2 (Air)	V _{ESD}	± 30	kV
ESD per IEC 61000-4-2 (Contact)		± 30	
Operating Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{STJ}	-55 to +150	°C

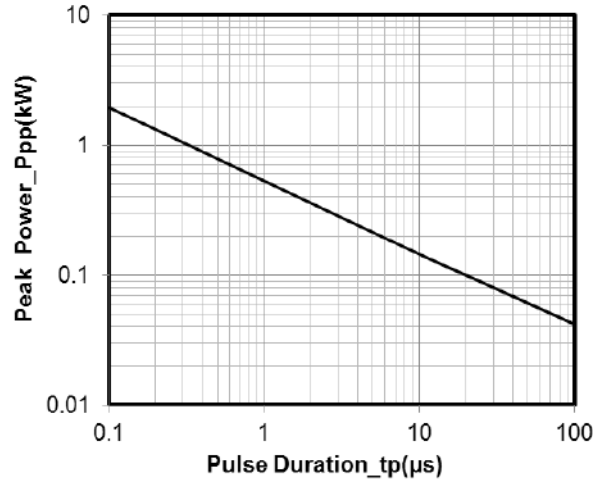
Electrical Characteristics (TA=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Working Voltage	V_{RWM}				5	V
Breakdown Voltage	V_{BR}	$I_T = 1mA$	5.6	6.5	8.0	V
Reverse Leakage Current	I_R	$V_{RWM} = 5V$			0.1	μA
Clamping Voltage	V_C	$I_{PP} = 1A$ (8 x 20 μs pulse)			8	V
Clamping Voltage	V_C	$I_{PP} = 8A$ (8 x 20 μs pulse)			11	V
Junction Capacitance	C_J	$V_R = 0V$, $f = 1MHz$		15		pF

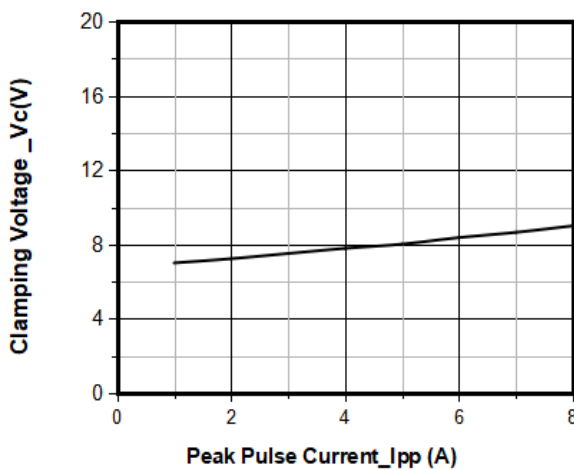
Typical Performance Characteristics (TA=25°C unless otherwise specified)



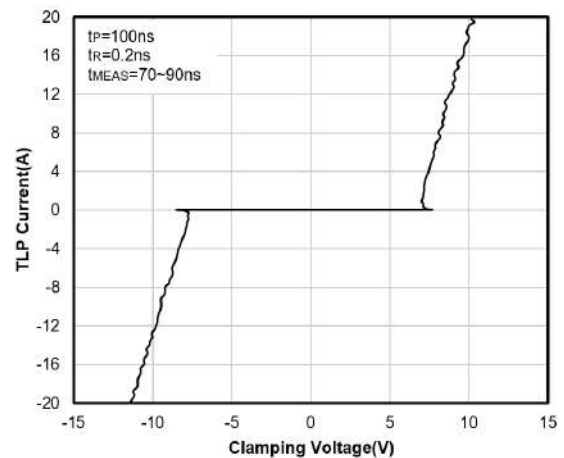
Junction Capacitance vs. Reverse Voltage



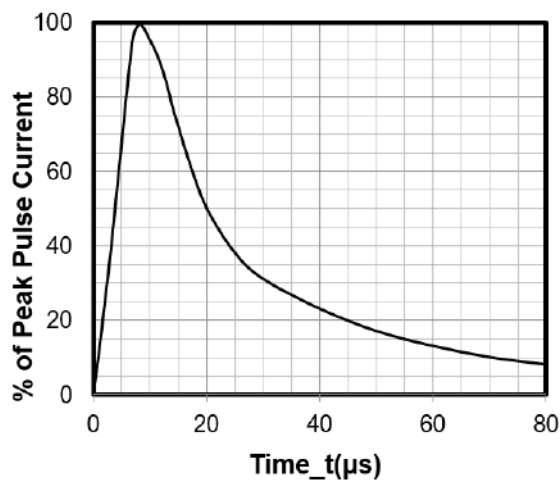
Peak Pulse Power vs. Pulse Time



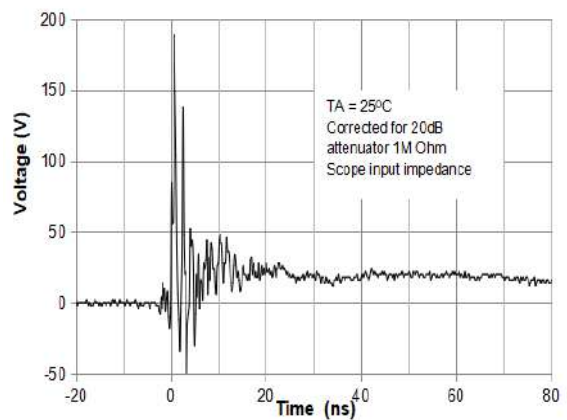
Clamping Voltage vs. Peak Pulse Current (tp = 8/20 μs)



TLP Curve



8 X 20 μs Pulse Waveform



ESD Clamping Voltage
8 kV Contact per IEC61000-4-2

